



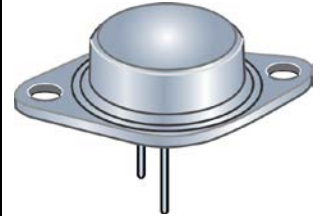
## PNP Darlington Power Silicon Transistor

Qualified per MIL-PRF-19500/505

Qualified Levels:  
JAN, JANTX, and  
JANTXV

### DESCRIPTION

This high speed PNP transistor is rated at 20 amps and is military qualified up to a JANTXV level. This TO-204AA isolated package features a 180 degree lead orientation.



**Important:** For the latest information, visit our website <http://www.microsemi.com>.

### FEATURES

- JEDEC registered 2N6286 and 2N6287
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/505
- RoHS compliant versions available (commercial grade only)

**TO-204AA (TO-3)  
Package**

### APPLICATIONS / BENEFITS

- Military, space and other high reliability applications
- High frequency response
- TO-204AA case with isolated terminals

### MAXIMUM RATINGS @ T<sub>C</sub> = +25 °C unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T <sub>J</sub> and T <sub>STG</sub>	-65 to +175	°C
Thermal Resistance Junction-to-Case	R <sub>θJC</sub>	0.855	°C/W
Collector Current	I <sub>C</sub>	-20	A
Collector-Emitter Voltage	V <sub>CEO</sub>	2N6286 -80	V
		2N6287 -100	
Collector-Base Voltage	V <sub>CBO</sub>	2N6286 -80	V
		2N6287 -100	
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Total Power Dissipation	P <sub>T</sub>	@ T <sub>C</sub> = +25 °C <sup>(1)</sup>	175
		@ T <sub>C</sub> = +100 °C	87.5

**Notes:** 1. Derate linearly 1.0 W/°C above T<sub>C</sub> > +25 °C

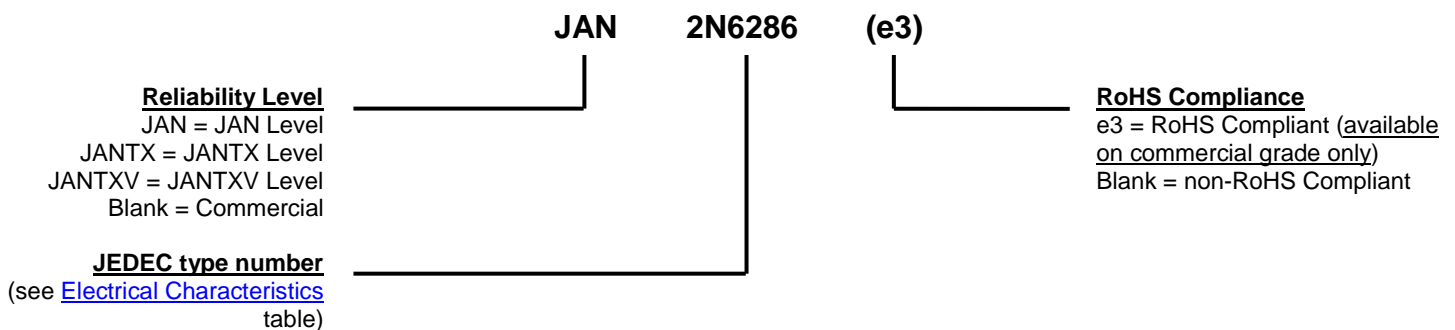
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**MECHANICAL and PACKAGING**

- CASE: Industry standard TO-204AA (TO-3), hermetically sealed, 0.040 inch diameter pins
- FINISH: Solder dipped tin-lead over nickel plated alloy 52 or RoHS compliant matte-tin plating. Solderable per MIL-STD-750 method 2026.
- POLARITY: PNP (see [schematic](#))
- MOUNTING HARDWARE: Consult factory for optional insulator and sheet metal screws
- WEIGHT: Approximately 15 grams
- See [package dimensions](#) on last page.

**PART NOMENCLATURE**

**SYMBOLS & DEFINITIONS**

Symbol	Definition
$I_B$	Base current: The value of the dc current into the base terminal.
$I_C$	Collector current: The value of the dc current into the collector terminal.
$I_E$	Emitter current: The value of the dc current into the emitter terminal.
$T_C$	Case temperature: The temperature measured at a specified location on the case of a device.
$V_{CB}$	Collector-base voltage: The dc voltage between the collector and the base.
$V_{CBO}$	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.
$V_{CC}$	Collector-supply voltage: The supply voltage applied to a circuit connected to the collector.
$V_{CEO}$	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.
$V_{EB}$	Emitter-base voltage: The dc voltage between the emitter and the base.
$V_{EBO}$	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.

**ELECTRICAL CHARACTERISTICS @  $T_A = +25^\circ\text{C}$  unless otherwise noted**

Characteristics	Symbol	Min.	Max.	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage $I_C = -100\text{ mA}$	2N6286 2N6287	$V_{(BR)CEO}$	-80 -100	V
Collector-Emitter Cutoff Current $V_{CE} = -40\text{ V}$ $V_{CE} = -50\text{ V}$	2N6286 2N6287	$I_{CEO}$	-1.0 -1.0	mA
Collector-Emitter Cutoff Current $V_{CE} = -80\text{ V}, V_{BE} = +1.5\text{ V}$ $V_{CE} = -100\text{ V}, V_{BE} = +1.5\text{ V}$	2N6286 2N6287	$I_{CEX}$	10 10	$\mu\text{A}$
Emitter-Base Cutoff Current $V_{EB} = -7.0\text{ V}$		$I_{EBO}$	-2.5	mA

**ON CHARACTERISTICS**

Forward-Current Transfer Ratio $I_C = -1.0\text{ A}, V_{CE} = -3.0\text{ V}$ $I_C = -10\text{ A}, V_{CE} = -3.0\text{ V}$ $I_C = -20\text{ A}, V_{CE} = -3.0\text{ V}$		$h_{FE}$	1,500 1,250 300	18,000
Collector-Emitter Saturation Voltage $I_C = -20\text{ A}, I_B = -200\text{ mA}$ $I_C = -10\text{ A}, I_B = -40\text{ mA}$		$V_{CE(sat)}$	-3.0 -2.0	V
Base-Emitter Saturation Voltage $I_C = -20\text{ A}, I_B = -200\text{ mA}$		$V_{BE(sat)}$	-4.0	V
Base-Emitter Voltage Non-saturated $V_{CE} = -3.0\text{ V}, I_C = -10\text{ A}$		$V_{BE}$	-2.8	V

**DYNAMIC CHARACTERISTICS**

Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = -10\text{ A}, V_{CE} = -3.0\text{ V}, f = 1\text{ kHz}$		$h_{fe}$	300	
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = -10\text{ A}, V_{CE} = -3.0\text{ V}, f = 1\text{ MHz}$		$ h_{fe} $	8	80
Output Capacitance $V_{CB} = -10\text{ V}, I_E = 0, 100\text{ kHz} \leq f \leq 1\text{ MHz}$		$C_{obo}$	400	pF

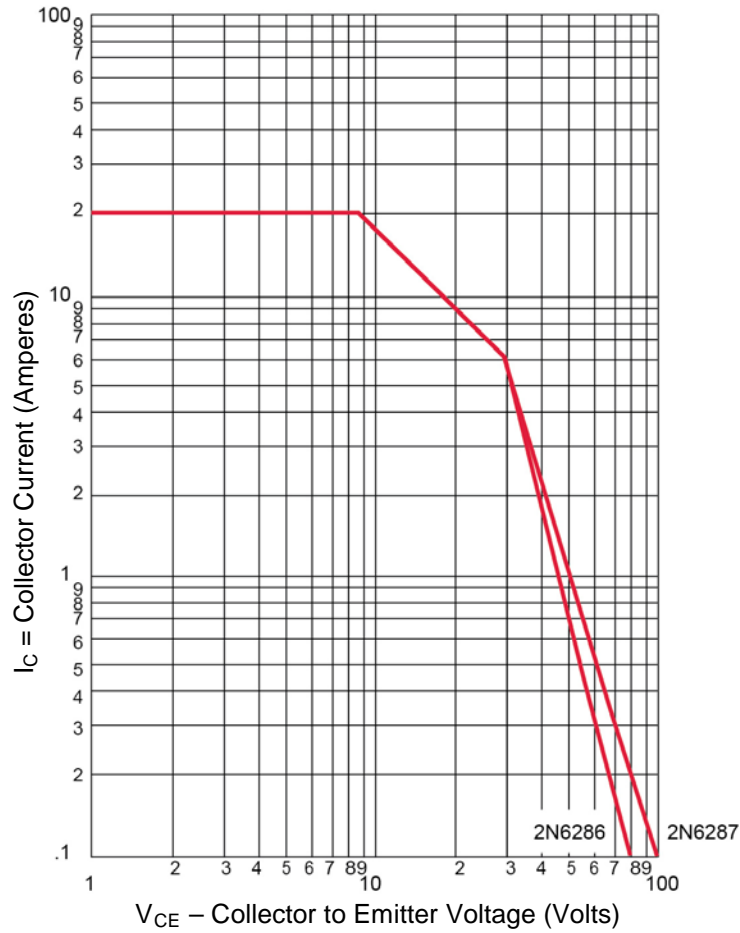
**ELECTRICAL CHARACTERISTICS @  $T_C = 25^\circ\text{C}$  unless otherwise noted. (continued)**
**SWITCHING CHARACTERISTICS**

Turn-On Time $V_{CC} = -30\text{ V}, I_C = -10\text{ A}; I_B = -40\text{ mA}$	$t_{on}$		2.0	$\mu\text{s}$
Turn-Off Time $V_{CC} = -30\text{ V}, I_C = -10\text{ A}; I_{B1} = I_{B2} = -40\text{ mA}$	$t_{off}$		10	$\mu\text{s}$

**SAFE OPERATING AREA (See figures 1 and 2 and [MIL-STD-750, Test Method 3053](#))**
**DC Tests**
 $T_C = +25^\circ\text{C}, t = 1\text{ second}, 1\text{ Cycle}$ 
**Test 1**
 $V_{CE} = -8.75\text{ V}, I_C = -20\text{ A}$ 
**Test 2**
 $V_{CE} = -30\text{ V}, I_C = -5.8\text{ A}$ 
**Test 3**
 $V_{CE} = -80\text{ V}, I_C = -100\text{ mA}$  (2N6286)

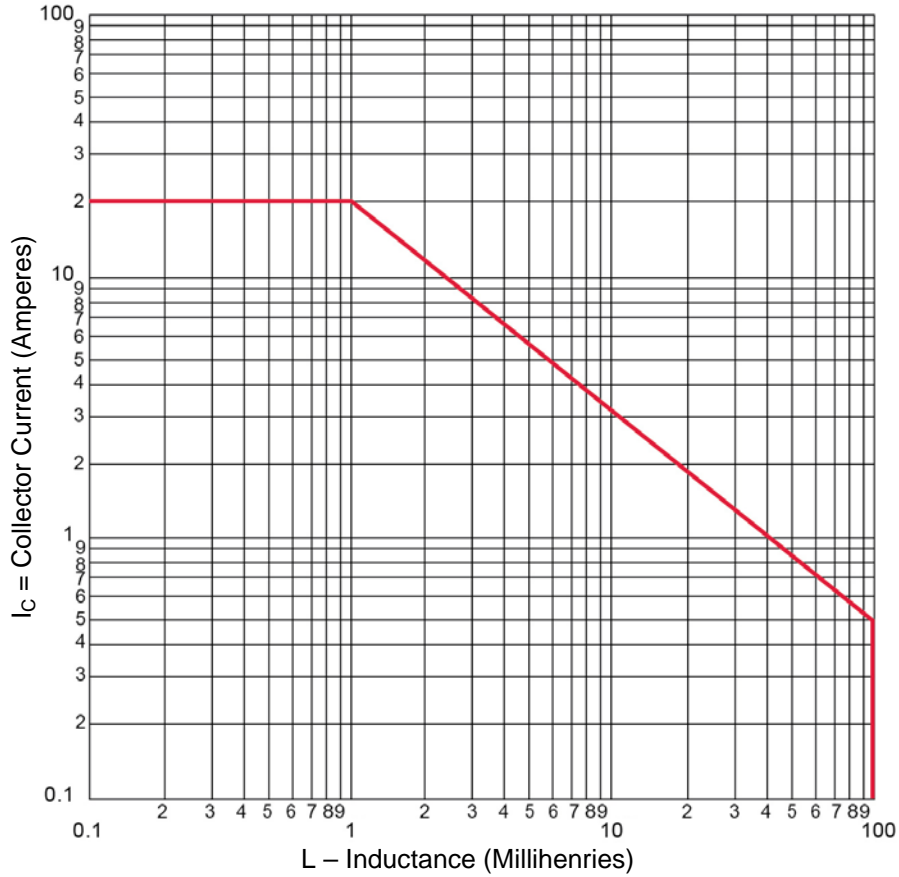
 $V_{CE} = -100\text{ V}, I_C = -100\text{ mA}$  (2N6287)

**SAFE OPERATING AREA**



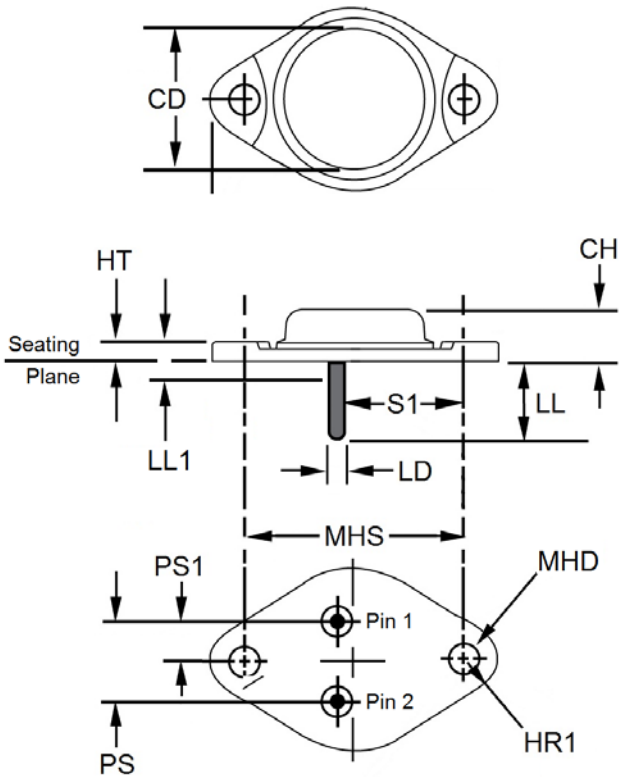
**FIGURE 1**  
Maximum Safe Operating Area Graph  
 (continuous dc)

**SAFE OPERATING AREA (continued)**



**FIGURE 2**  
Safe Operating Area For Switching Between Saturation And Cutoff  
 (unclamped inductive load).

PACKAGE DIMENSIONS

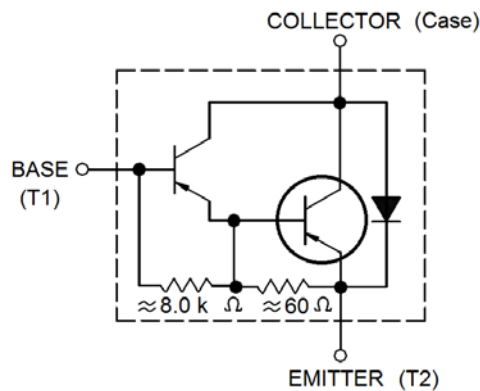


Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	-	0.875	-	22.23	3
CH	0.250	0.360	6.35	9.14	
HR	0.495	0.525	12.57	13.34	
HR1	0.131	0.188	3.33	4.78	
HT	0.060	0.135	1.52	3.43	
LD	0.038	0.043	0.97	1.09	4, 8
LL	0.312	0.500	7.92	12.70	4
LL1	-	0.050	-	1.27	4, 8
MHD	0.151	0.165	3.84	4.19	6
MHS	1.177	1.197	29.90	30.40	
PS	0.420	0.440	10.67	11.18	3
PS1	0.205	0.225	5.21	5.72	
S1	0.655	0.675	16.64	17.15	
T1	Emitter				
T2	Base				
Case	Collector				

NOTES:

1. Dimensions are in inches. Millimeters are given for information only.
2. Body contour is optional within zone defined by CD
3. These dimensions shall be measured at points 0.050 inch (1.27 mm) to 0.055 inch (1.40 mm) below seating plane.
4. Both terminals
5. At both ends
6. Two holes
7. Terminal 1 is the emitter, terminal 2 is base. The collector shall be electrically connected to the case.
8. LD applies between L1 and LL. Diameter is uncontrolled in L1.
9. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi$ x symbology.

SCHEMATIC



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